

isc Silicon PNP Power Transistor

2SA1244

DESCRIPTION

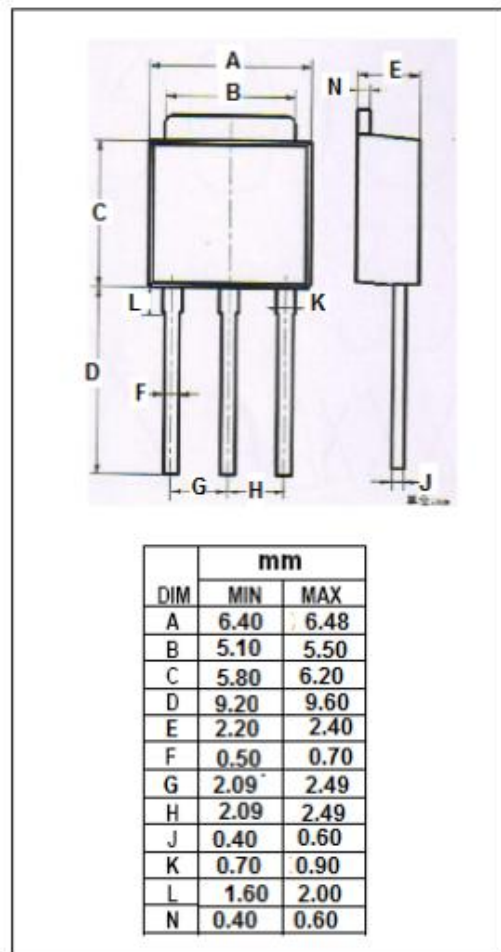
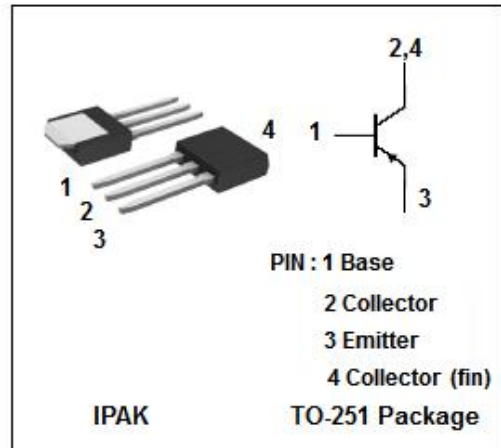
- With TO-251(IPAK) packaging
- High speed switching time
- Low collector saturation voltage
- Complement to type 2SC3074
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Medium power dissipation

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	-60	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current-Continuous	-5	A
I _B	Base Current	-1	A
P _C	Collector Power Dissipation @ T _C =25°C	20	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



isc Silicon PNP Power Transistor**2SA1244****ELECTRICAL CHARACTERISTICS** $T_c=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -3A; I_B = -0.15A$			-0.4	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -3A; I_B = -0.15A$			-1.2	V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -10mA; I_B = 0$	-50			V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -50V; I_E = 0$			-1.0	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5V; I_C = 0$			-1.0	μA
h_{FE1}	DC Current Gain	$I_C = -1A; V_{CE} = -1V$	70		240	
h_{FE1}	DC Current Gain	$I_C = -3A; V_{CE} = -1V$	30			

◆ **h_{FE1} Classifications**

O	Y
70-140	120-240